

**SANYO**

No. 1853A

**2SA1434**

PNP Epitaxial Planar Silicon Transistor  
 High  $h_{FE}$ , Low-Frequency  
 General-Purpose Amp Applications

**Applications**

- Low frequency general-purpose amplifiers, drivers, muting circuits

**Features**

- Very small-sized package permitting 2SA1434-used sets to be made smaller, slimmer.
- Adoption of FBET process
- High DC current gain ( $h_{FE}=500$  to  $1200$ )
- Low collector-to-emitter saturation voltage ( $V_{CE(sat)} \leq 0.5V$ )
- High  $V_{EBO}$  ( $V_{EBO} \geq 15V$ )

**Absolute Maximum Ratings at  $T_a=25^\circ C$** 

			unit
Collector to Base Voltage	$V_{CB0}$	-60	V
Collector to Emitter Voltage	$V_{CE0}$	-50	V
Emitter to Base Voltage	$V_{EBO}$	-15	V
Collector Current	$I_C$	-100	mA
Collector Current(Pulse)	$I_{CP}$	-200	mA
Collector Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	125	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 125	$^\circ C$

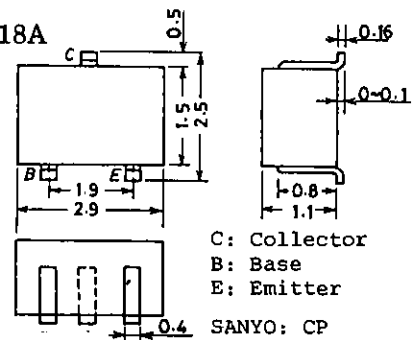
**Electrical Characteristics at  $T_a=25^\circ C$** 

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=-10V, I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=-5V, I_C=-10mA$	500	800	1200	
Gain-Bandwidth Product	$f_T$	$V_{CE}=-10V, I_C=-10mA$		100		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=-10V, f=1MHz$		4.8		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-1mA$	-0.2	-0.5		V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50mA, I_B=-1mA$	-0.8	-1.1		V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-50			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-15			V

Marking :FL

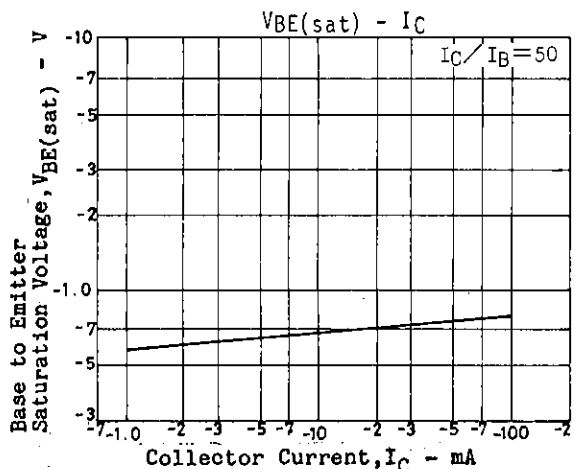
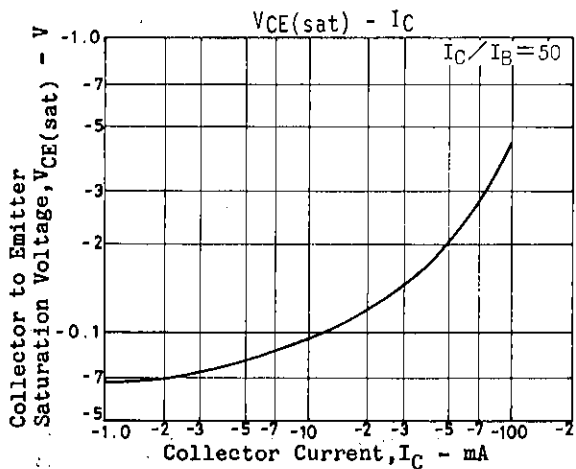
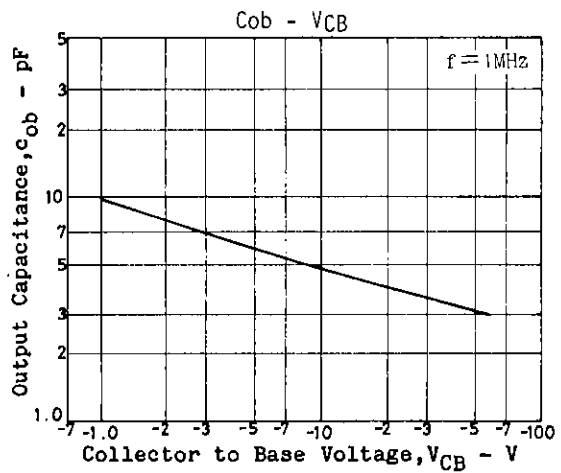
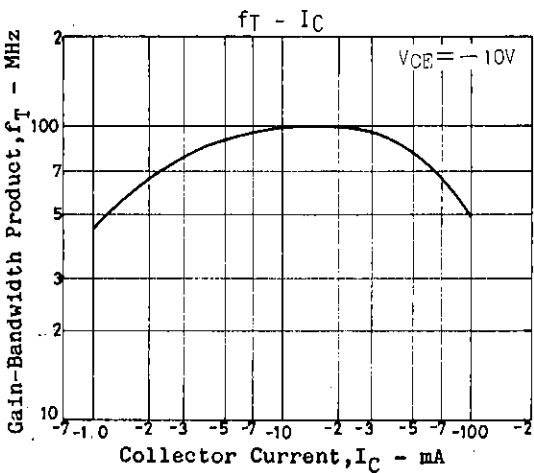
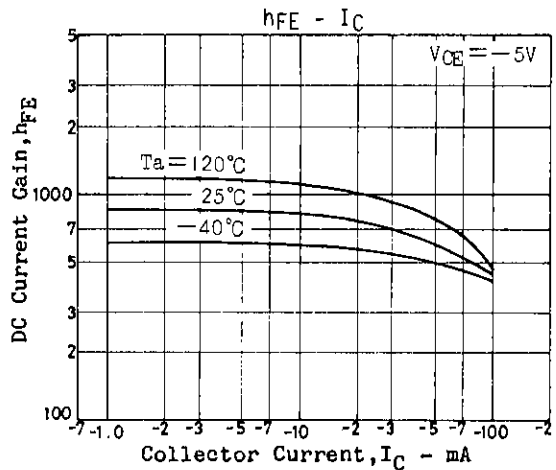
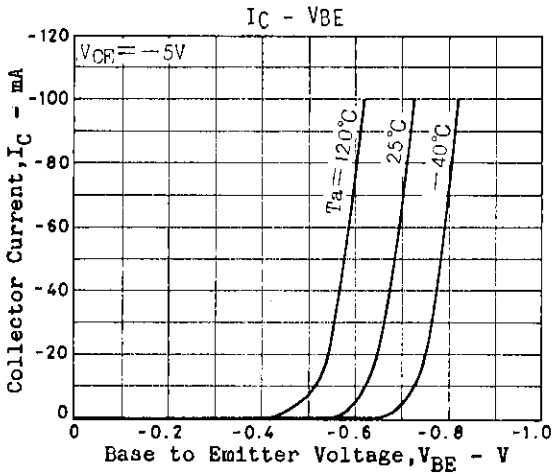
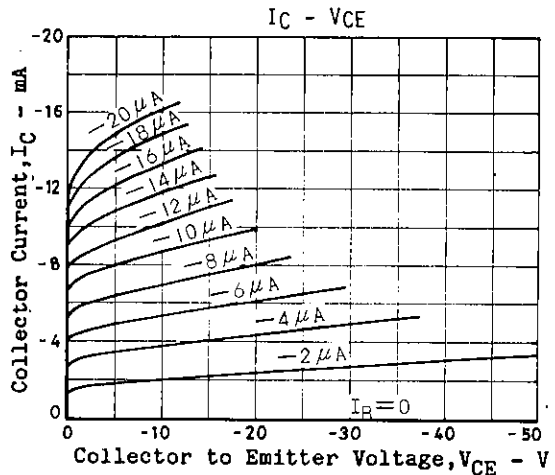
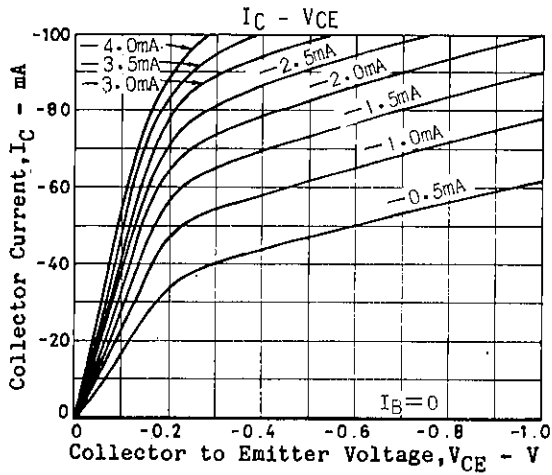
**Package Dimensions 2018A**

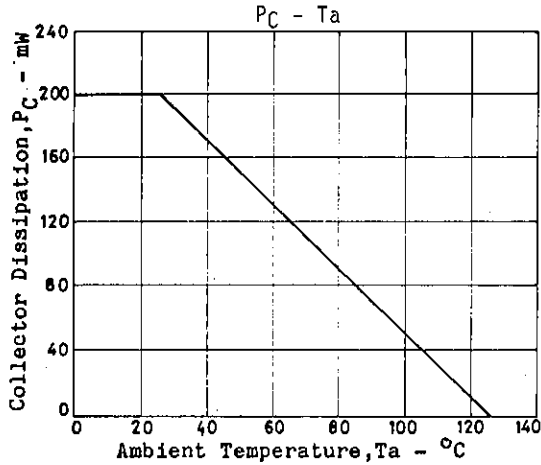
(unit:mm)

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